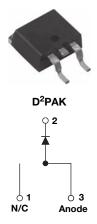
Vishay Semiconductors

### HEXFRED<sup>®</sup>, Ultrafast Soft Recovery Diode, 4 A



PRODUCT SUMMARY							
Package TO-263AB (D <sup>2</sup> PAK)							
I <sub>F(AV)</sub>	4 A						
V <sub>R</sub>	600 V						
V <sub>F</sub> at I <sub>F</sub>	1.8 V						
t <sub>rr</sub> (typ.)	17 ns						
T <sub>J</sub> max.	150 °C						
Diode variation	Single die						

#### FEATURES

- Ultrafast recovery
- Ultrasoft recovery
- Very low I<sub>RRM</sub>
- $\bullet$  Very low  $\mathsf{Q}_{\mathsf{rr}}$
- Specified at operating temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
   FREE
- AEC-Q101 qualified
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

#### DESCRIPTION

VS-HFA04TB60S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 4 A continuous current, the VS-HFA04TB60S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the  $t_b$  portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA04TB60S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V <sub>R</sub>		600	V			
Maximum continuous forward current	١ <sub>F</sub>	T <sub>C</sub> = 100 °C	4				
Single pulse forward current	I <sub>FSM</sub>		25	А			
Maximum repetitive forward current	I <sub>FRM</sub>		16				
Maximum namer dissinction	PD	T <sub>C</sub> = 25 °C	25	W			
Maximum power dissipation		T <sub>C</sub> = 100 °C	10	vv			
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 55 to + 150	°C			

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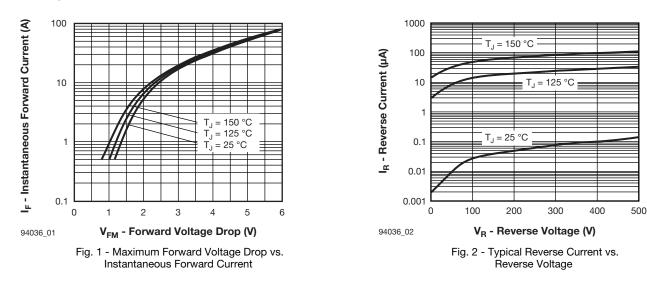
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<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA		600	-	-			
Maximum forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 4.0 A		-	1.5	1.8	V		
		I <sub>F</sub> = 8.0 A	See fig. 1	-	1.8	2.2			
		I <sub>F</sub> = 4.0 A, T <sub>J</sub> = 125 °C		-	1.4	1.7			
Maximum reverse			Coofig 0	-	0.17	3.0			
leakage current	I <sub>RM</sub>	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See fig. 2	-	44	300	μA		
Junction capacitance	CT	V <sub>R</sub> = 200 V See fig. 3		-	4.0	8.0	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body - 8.0 - r				nH			

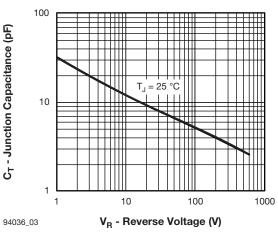
DYNAMIC RECOVERY CHARACTERISTICS (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	PARAMETER SYMBOL TEST CONDITIONS							
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}$	√μs, V <sub>R</sub> = 30 V	-	17	-		
Reverse recovery time See fig. 5, 6	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 4.0 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	28	42	ns	
000 lig. 5, 0	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	38	57		
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	2.9	5.2	A nC	
reak recovery current	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	3.7	6.7		
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	40	60		
See fig. 7	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	70	105		
Peak rate of fall of recovery current during t <sub>b</sub> See fig. 8	dl <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	280	-	A/µs	
	dl <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	235	-	Ανμδ	

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	MIN.	TYP.	MAX.	UNITS					
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	5.0	K/W			
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	- <b>N∕ VV</b>			
Weight			-	2.0	-	g			
weight			-	0.07	-	oz.			
Marking device		Case style D <sup>2</sup> PAK		HFA04TB60S					

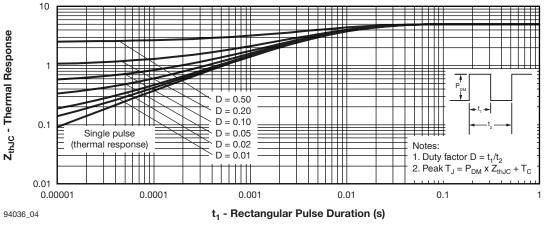
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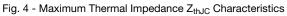


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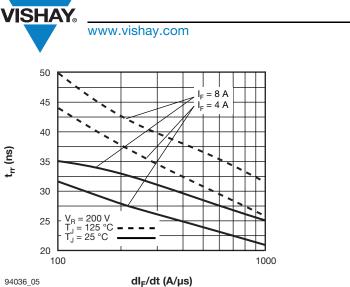


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Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

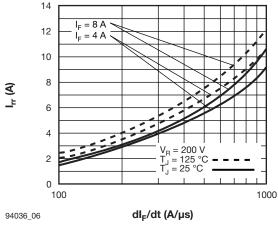


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

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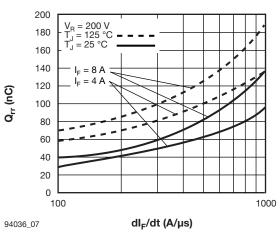
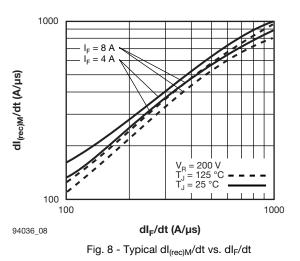
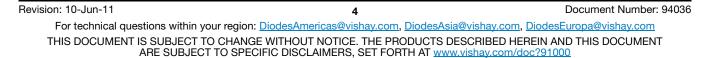


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt







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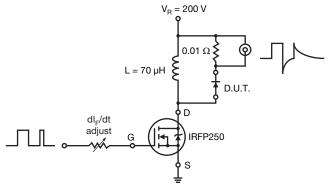


Fig. 9 - Reverse Recovery Parameter Test Circuit

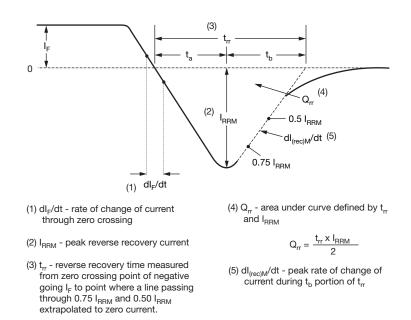


Fig. 10 - Reverse Recovery Waveform and Definitions

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#### **ORDERING INFORMATION TABLE**

Device code	VS-	HF	Α	04	тв	60	S	TRL	PbF
	1	2	3	4	5	6	7	8	9
	1 -		⊃ produ XFRED <sup>@</sup>						
	3 - Process designator: A = Electron irradiated								
	4 -	Cur	rent rati	ng (04 =	= 4 A)				
	5 -	- Package outline (TB = TO-220, 2 leads)							
	6 -	Volt	tage rati	ng (60 =	= 600 V)				
	7 -	S =	D <sup>2</sup> PAK						
	8 -	• N	one = T	ube (50	pieces)				
	<ul> <li>TRL = Tape and reel (left oriented)</li> </ul>								
	<ul> <li>TRR = Tape and reel (right oriented)</li> </ul>								
	9 - PbF = Lead (Pb)-free								

LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95046						
Part marking information	www.vishay.com/doc?95054					
Packaging information	www.vishay.com/doc?95032					



### **Outline Dimensions**

**Vishay Semiconductors** 

D<sup>2</sup>PAK



Conforms to JEDEC outline D<sup>2</sup>PAK (SMD-220) в Pad layout (2)(3)A 11.00 .... MIN.→ (E) F (0.43)(3) L1 4 (0.38)<sup>MIN.</sup> (D1) (3) Detail A D 17.90 (0.70) Н 15.00 (0.625) (2) З (0.15) MIN. Ľ L2 Ĥ ţ В В 2.32 MIN. (0.08) 2.64 (0.103) 2.41 (0.096) (3)Г 2 x b2 С View A - A 2 x h // ± 0.004 🕅 B ⊕ 0.010 M A M B Base Plating (4) Metal 2 x e Н b1. b3 Gauge plane c1 (4) (c) В 0° to 8° ŧ. Seating Lead assignments plane L3 A1 Lead tip (b, b2) Diodes Section B - B and C - C 1. - Anode (two die)/open (one die) Scale: None 2., 4. - Cathode Detail "A" Rotated 90 °CW

Scale: 8:1

3. - Anode

MILLIMETERS INCHES SYMBOL NOTES MIN. MIN. MAX. MAX. А 4.06 4.83 0.160 0.190 0.00 A1 0.254 0.000 0.010 b 0.51 0.99 0.020 0.039 0.51 0.89 0.020 0.035 4 b1 b2 1.14 1.78 0.045 0.070 1.14 1.73 b3 0.045 0.068 4 0.38 0.74 0.015 0.029 с 0.38 0.58 c1 0.015 0.023 4 c2 1.14 1.65 0.045 0.065 D 8.51 9.65 0.335 0.380 2

SYMBOL	MILLIM	IETERS	INC	NOTES	
STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010	BSC	
L4	4.78	5.28	0.188	0.208	

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

<sup>(7)</sup> Outline conforms to JEDEC outline TO-263AB

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#### **DIMENSIONS** in millimeters and inches



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